

IN THE ABSTRACT:

Please amend the Substitute Abstract as follows:

C1
--A process gas consisting of ~~containing any~~ one of N_2 , or N_2O or a mixture thereof is converted to a plasma and then a surface of a copper wiring layer is exposed to the plasma of the process gas, whereby a surface portion of the copper wiring layer is reformed and made into a copper diffusion preventing barrier. According to this method, a noble semiconductor device can be provided having increased operational speed and less copper diffusion. --
